

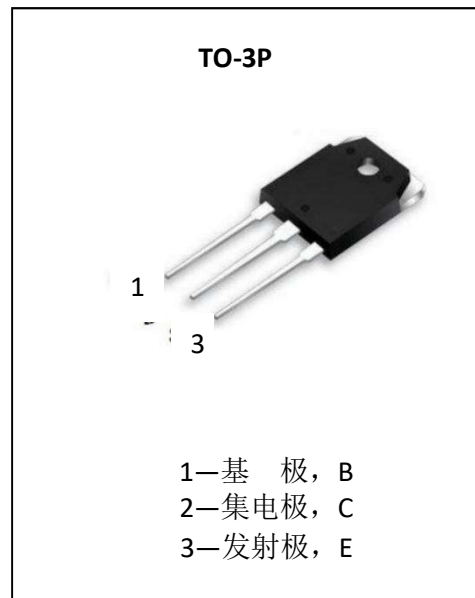
主要用途

高压快速开关

极限值 ($T_a=25^{\circ}\text{C}$)

T_{stg} — 贮存温度	- 65 ~ 150 $^{\circ}\text{C}$
T_j — 结温	150 $^{\circ}\text{C}$
P_C — 集电极耗散功率 ($T_c=25^{\circ}\text{C}$)	100W
V_{CBO} — 集电极—基极电压	700V
V_{CEO} — 集电极—发射极电压	400V
V_{EBO} — 发射极—基极电压	9V
I_C — 集电极电流 (DC)	12A
I_B — 基极电流	6A

外形图及引脚排列



电参数 ($T_a=25^{\circ}\text{C}$)

参数符号	符 号 说 明	最小值	典型值	最大值	单 位	测 试 条 件
B_{VCEO}	集电极—发射极击穿电压	400			V	$I_C=10\text{mA}, I_B=0$
I_{EBO}	发射极—基极截止电流			1	mA	$V_{\text{EB}}=9\text{V}, I_C=0$
$H_{\text{FE}} (1)$	直流电流增益	8		40		$V_{\text{CE}}=5\text{V}, I_C=3\text{A}$
$H_{\text{FE}} (2)$		6		30		$V_{\text{CE}}=5\text{V}, I_C=5\text{A}$
$V_{\text{CE}} (\text{sat})$	集电极—发射极饱和压降			1	V	$I_C=5\text{A}, I_B=1\text{A}$
				1.5	V	$I_C=8\text{A}, I_B=1.6\text{A}$
				3	V	$I_C=12\text{A}, I_B=3\text{A}$
$V_{\text{BE}} (\text{sat})$	基极—发射极饱和压降			1.2	V	$I_C=5\text{A}, I_B=1\text{A}$
				1.6	V	$I_C=8\text{A}, I_B=1.6\text{A}$
C_{ob}	共基极输出电容		180		pF	$V_{\text{CB}}=10\text{V}, f=0.1\text{MHz}$
f_T	特征频率	4			MHz	$V_{\text{CE}}=10\text{V}, I_C=0.5\text{A}$
t_{ON}	导通时间			1.1	μS	$V_{\text{CC}}=125\text{V}, I_C=8\text{A}$
t_{STG}	贮存时间			3.0	μS	$I_{\text{B1}}=I_{\text{B2}}=1.6\text{A}$
t_F	下降时间			0.7	μS	

■ 特性曲线

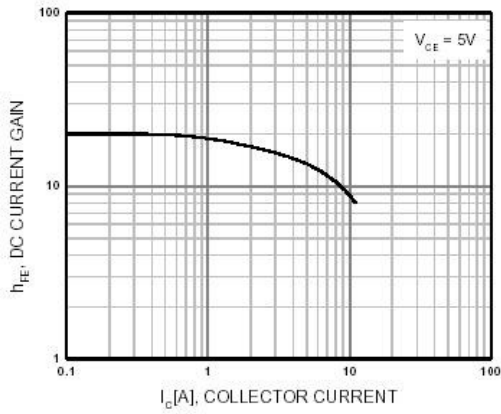


Figure 1. DC current Gain

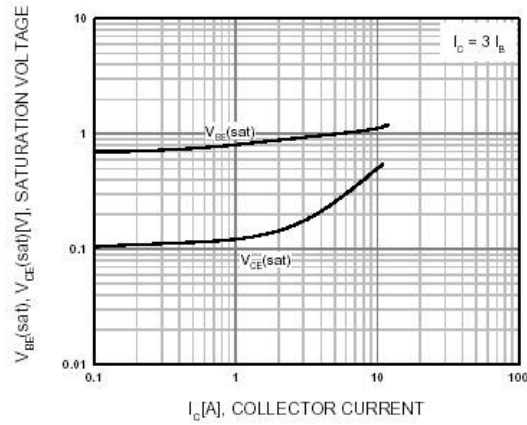


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

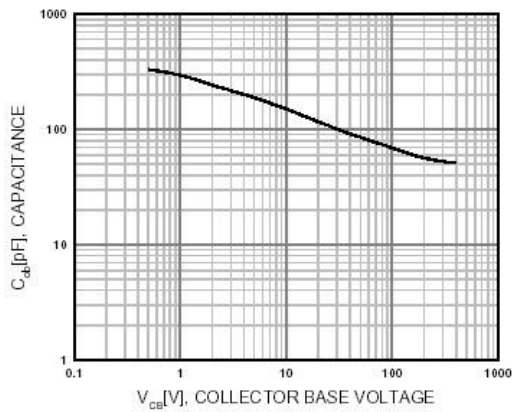


Figure 3. Collector Output Capacitance

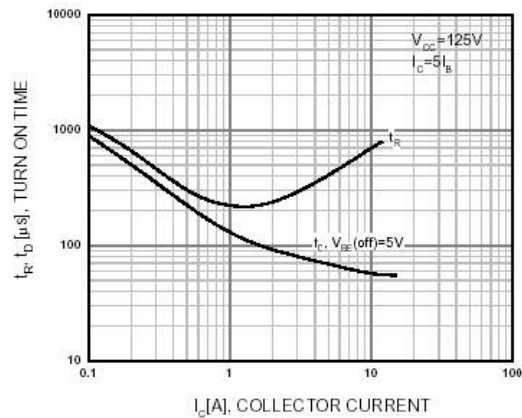


Figure 4. Turn On Time

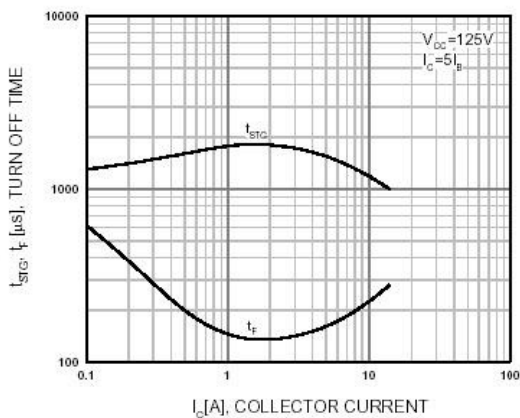


Figure 5. Turn Off Time

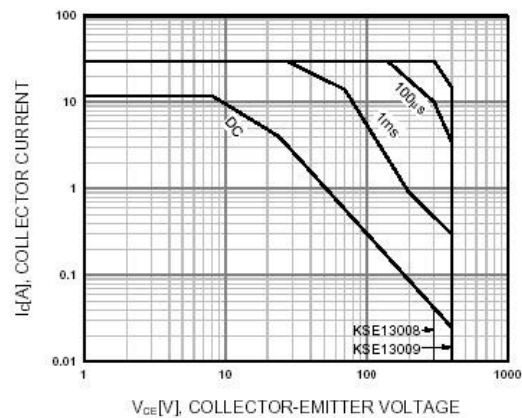


Figure 6. Safe Operating Area

■ 特性曲线

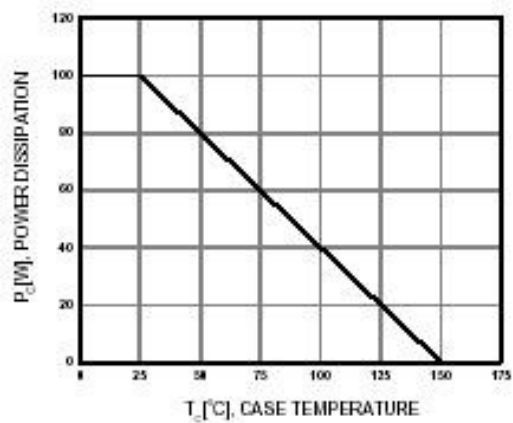


Figure 7. DC current Gain



迈诺斯科技

E13009L-MNS

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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